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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Application Number	10/068,928
				Filing Date	February 7, 2002
				Applicant(s)	Yee-Chia Yeo, et al.
				Art Unit	2814
				Examiner Name	Theresa T. Doan
SHEET	1	OF	1	Attorney Docket Number	(formerly TS01-1379) 2001-1379 / 24061.421

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document

FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

NON-PATENT LITERATURE DOCUMENTS		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
TD	AA	YANG-KYU CHOI ET AL., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era", IEEE Electron Device Letters, Vol. 21, No. 5, May 2000, pps. 254-255.
TD	AB	YANG-KYU CHOI ET AL., "30nm Ultra-Thin-Body SOI MOSFET with Selectively Deposited Ge Raised S/D", Device Research Conference, Denver, CO., June 2000, pps. 23-24.
TD	AC	Hon-Sum Wong ET AL. "Three-Dimensional Atomistic Simulation of Discrete Random Dopant Distribution Effects in Sub-0.1 um MOSFET's", International Electron Device Meeting Tech. Digest, December 1993, pps. 705-708.
TD	AD	L.-J. HUANG ET AL, "Carrier Mobility Enhancement in Strained Si-On-Insulator Fabricated by Wafer Bonding", 2001 Symposium on VLSI Technology Digest of Technical Papers, Kyoto, Japan, June 2001, pps. 57-58.
TD	AE	KERN (KEN) RIM ET AL., "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET'S", IEEE Transactions on Electron Devices, Vol. 47, No. 7, July 2000, pps. 1406-1415.
TD	AF	MICHAEL I. CURRENT ET AL., "Atomic-layer Cleaving with Si <sub>x</sub> Ge <sub>y</sub> Strain Layers for Fabrication of Si and Ge-rich Device Layers", 2001 IEEE International SOI Conference, October 2001, pps. 11-12.

Examiner Signature	<i>TD</i>	Date Considered	11/30/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.